Product data sheet

1. General description

AC Thyristor power switch in a SOT223 surface-mountable plastic package with self-protective capabilities against low and high energy transients.

2. Features and benefits

- · Common terminal on mounting base allows multiple ACTs on shared cooling pad
- Exclusive negative gate triggering
- Full cycle AC conduction
- High voltage capability
- · Remote gate separates the gate driver from the effects of the load current
- Safe clamping of low energy over-voltage transients
- · Self-protective turn-on during high energy voltage transients
- Surface-mountable package
- Very high noise immunity

3. Applications

- Fan motor circuits
- Pump motor circuits
- · Lower-power highly inductive, resistive and safety loads
- · Contactors, circuit breakers, valves, dispensers and door locks

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 112 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	0.8	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	-	13	А
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	-	14.3	Α
T _j	junction temperature		-	-	125	°C
V _{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses; <u>Fig. 6</u>	-	-	2.5	kV

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; LD+ G-;$ $T_j = 25 \text{ °C}; Fig. 10$	1	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; LD- G-;$ $T_j = 25 \text{ °C}; Fig. 10$	1	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 12</u>	-	-	20	mA
V _T	on-state voltage	I _T = 1.1 A; T _j = 25 °C; <u>Fig. 13</u>	-	-	1.3	V
V _{CL}	clamping voltage	$I_{CL} = 0.1 \text{ mA}; t_p = 1 \text{ ms}; T_j = 25 \text{ °C}$	850	-	-	V
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 15	1000	-	-	V/µs
		V _{DM} = 402 V; T _j = 125 °C; exponential waveform; gate open circuit; <u>Fig. 15</u>	2000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 0.8 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s}; \text{ (snubberless condition)}; \text{ gate open circuit;}$ Fig. 16; Fig. 17	0.5	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	LD	load		1.0
2	CM	common	4	LD IA
3	G	gate		G- 0
4	СМ	common	☐1 ☐2 ☐3	СМ 001аај924

6. Ordering information

Table 3. Ordering information

Type number		Orderable part number		Small packing		Package
	Name		method	quantity	version	issue date
ACT108W-800E	SOT223	ACT108W-800EF	Reel	4000	SOT223	16-Mar-2006

7. Marking

Table 4. Marking codes

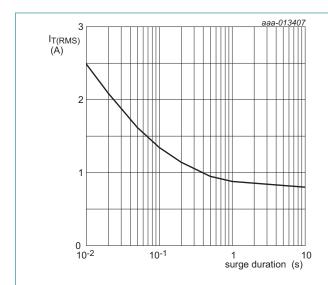
Type number	Marking codes
ACT108W-800E	108W8E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 112 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	0.8	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig 4; Fig 5	-	13	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	14.3	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.84	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 20 mA	-	100	A/µs
I _{GM}	peak gate current	t = 20 μs	-	1	А
V_{GM}	peak gate voltage	positive applied gate voltage	-	15	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C
V _{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses; Fig. 6	-	2.5	kV



f = 50 Hz; T_{sp} = 112 °C

Fig. 1. RMS on-state current as a function of surge duration; maximum values

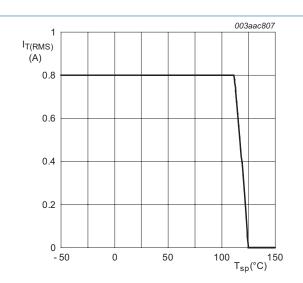
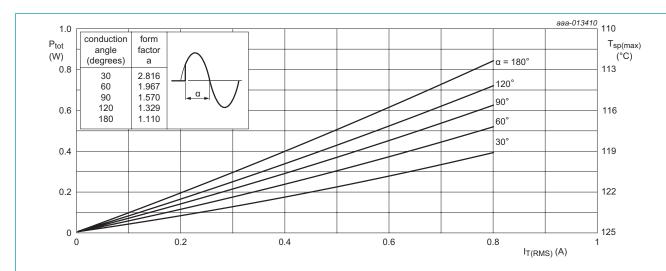


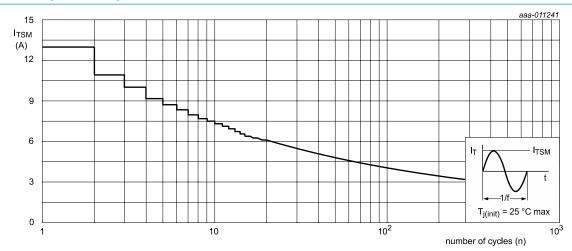
Fig. 2. RMS on-state current as a function of solder point temperature; maximum values



 α = conduction angle

a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

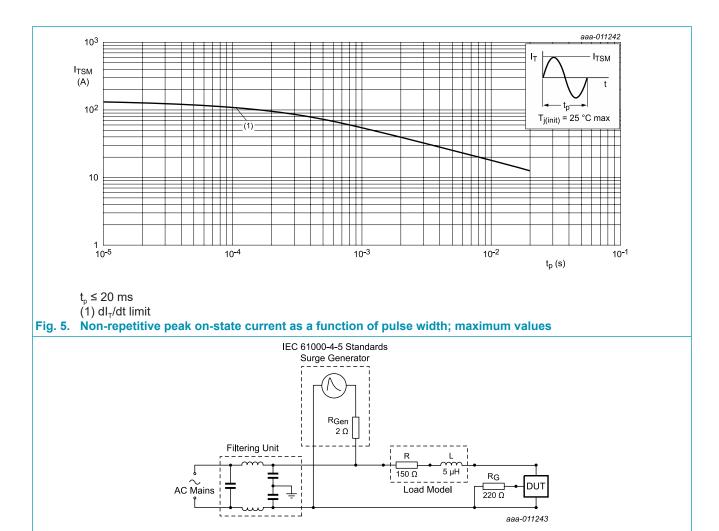


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-sp)}}$	thermal resistance from junction to solder point	full cycle with heatsink compound; Fig. 7	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to	in free air; printed circuit board mounted: minimum pad area; Fig. 8	-	70	-	K/W
	ambient free air	in free air; printed circuit board mounted: minimum footprint; Fig. 9	-	156	-	K/W

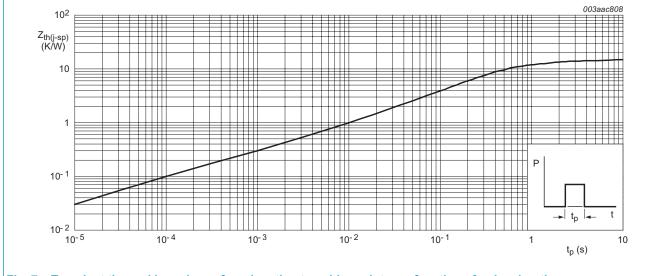
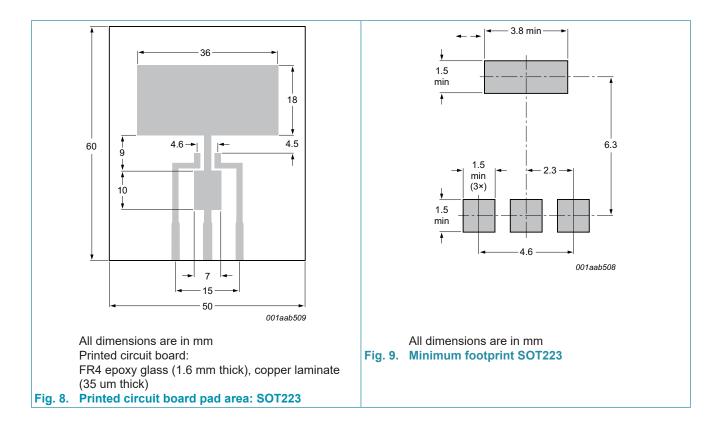


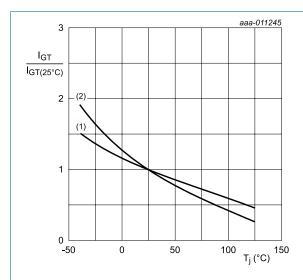
Fig. 7. Transient thermal impedance from junction to solder point as a function of pulse duration



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics		·			
l _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; LD+ G-;$ $T_j = 25 \text{ °C}; Fig. 10$	1	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; LD- G-;$ $T_j = 25 \text{ °C}; Fig. 10$	1	-	10	mA
I _L latching cu	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; LD+ G-;$ $T_j = 25 \text{ °C}; Fig. 11$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; LD- G-;$ $T_j = 25 \text{ °C}; Fig. 11$	-	-	20	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 12</u>	-	-	20	mA
V _T	on-state voltage	I _T = 1.1 A; T _j = 25 °C; <u>Fig. 13</u>	-	-	1.3	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 14	-	-	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C	0.15	-	-	V
I _D off-state current	off-state current	V _D = 800 V; T _j = 25 °C	-	-	2	mA
		V _D = 800 V; T _j = 125 °C	-	-	0.2	mA
V_{CL}	clamping voltage	$I_{CL} = 0.1 \text{ mA}; t_p = 1 \text{ ms}; T_j = 25 \text{ °C}$	850	-	-	V
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 15	1000	-	-	V/µs
		V_{DM} = 402 V; T_j = 125 °C; exponential waveform; gate open circuit; Fig. 15	2000	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit; Fig. 16; Fig. 17	0.5	-	-	A/ms



(1) LD+ G-(2) LD- G-

Fig. 10. Normalized gate trigger current as a function of junction temperature

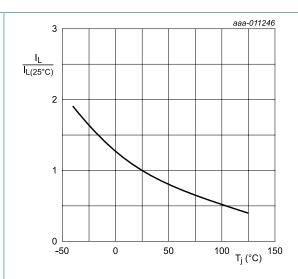


Fig. 11. Normalized latching current as a function of junction temperature

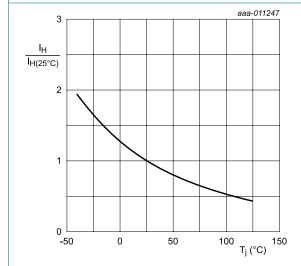
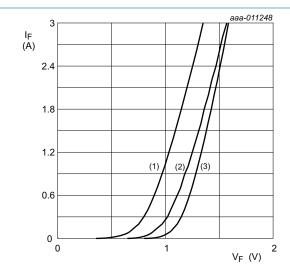


Fig. 12. Normalized holding current as a function of junction temperature



 V_o = 1.031 V; R_s = 0.1488 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 13. On-state current as a function of on-state voltage

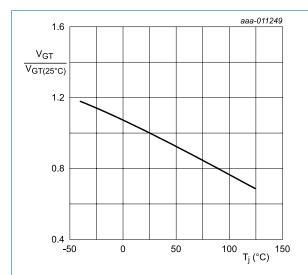
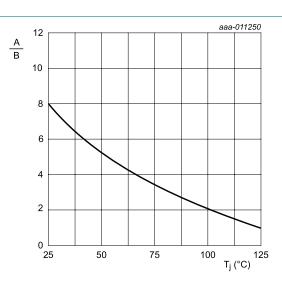
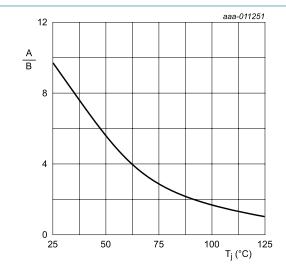


Fig. 14. Normalized gate trigger voltage as a function of junction temperature



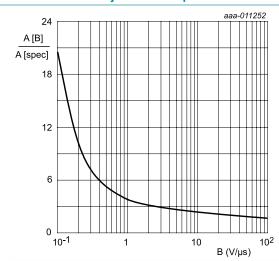
A = dV_D/dt at condition T_j °C B = dV_D/dt at condition T_j [125] °C

Fig. 15. Normalized rate of rise of off-state voltage as a function of junction temperature



A = dI_{com}/dt at condition T_j °C B = dI_{com}/dt at condition T_j [125] °C V_D = 400 V

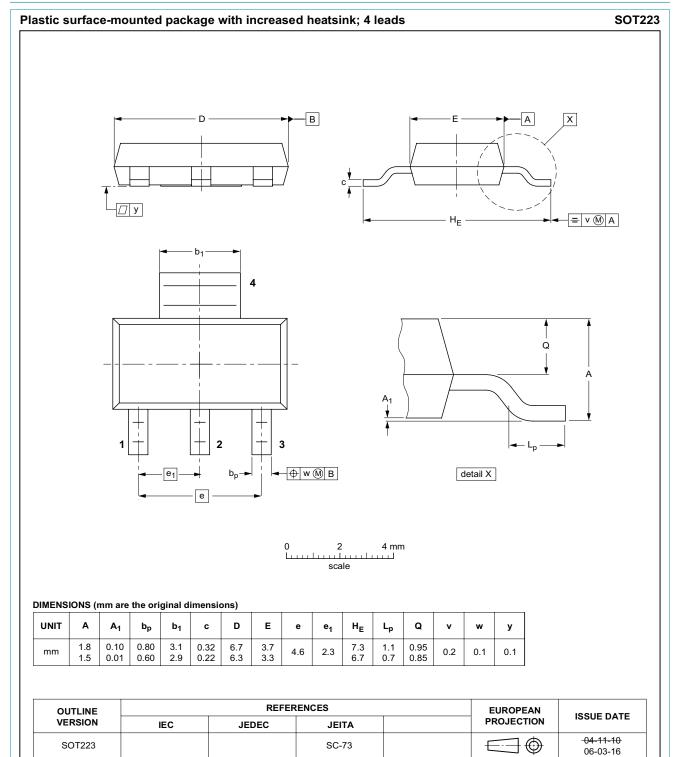
Fig. 16. Normalized critical rate of rise of commutating current as a function of junction temperature



A [B] = dI_{com}/dt at condition B, dV_{com}/dt A [spec] is the data sheet value for dI_{com}/dt turn-off time is less than 20 ms

Fig. 17. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

11. Package outline



PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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